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(54) REACTION VESSEL

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain a high quality reaction vessel excellent in corrosion resistance, heat impact resistance, etc., not causing any contamination and having a long life by forming the main body of the reaction vessel with a thermally decomposed boron nitride and coating an inner wall thereof with aluminum nitride.

SOLUTION: This reaction vessel is obtained by generating a thermally decomposed boron nitride having a very high impact resistance and no gas penetrating property by a chemical vapor phase deposition method, e.g. by reacting NH3 with BCl3 gas at $1600-2000^{\circ}$ C under 1-20Torr, forming a main body of the reaction vessel having 1-5mm thickness and a shape corresponding to the objective use, generating an aluminum nitride not corroded by oxygen or fluorine by a chemical vapor deposition method, e.g. by reacting NH3 with AlCl3 gas at $\leq 1100^{\circ}$ C under 1-10Torr, and coating the inner wall of the main body of the reaction vessel by $1-50\mu$ m thickness with the aluminum nitride having ≤ 100 nm crystallite size.

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(54)【発明の名称】 反応容器

(57)【要約】

【課題】 耐蝕性及び耐熱衝撃性に優れ、半導体製造分野、特にプラズマCVD反応装置用として好適な反応容器を得る。

【解決手段】 熱分解窒化硼素で形成された反応容器本体内壁に窒化アルミニウムを被覆する。

【特許請求の範囲】

【請求項1】 熱分解窒化硼素で形成された反応容器本体の内壁に窒化アルミニウムが被覆されてなることを特徴とする反応容器。

【請求項2】 内壁に被覆された窒化アルミニウムの結晶子サイズが100nm未満である請求項1記載の反応容器。

【請求項3】 プラズマCVD反応装置用である請求項1又は2記載の反応容器。

【発明の詳細な説明】

[0001]

【発明の属する技術分野】本発明は、半導体製造分野、特にはプラズマCVD反応装置用として好適な反応容器に関し、更に詳細には耐蝕性、耐熱衝撃性等に優れた反応容器に関する。

[0002]

【従来の技術】従来、プラズマCVD反応装置において、その反応容器の材質には金属が採用されてきたが、近年、反応性の高いガス種、例えば〇やFを使う反応が増えてきたことから、この反応容器の材質を腐食しやすい金属から耐蝕性の高いセラミックスへと変える動きがある。具体的には、アルミナ製や石英製の反応容器が採用され始めている。

[0003]

【発明が解決しようとする課題】しかし、反応容器をアルミナ製のものとすると、耐蝕性は飛躍的に向上するものの、アルミナは耐熱衝撃性が低く、反応による温度変化に耐えられず、容易に割れてしまうという欠点がある。更に、アルミナ製のものは通常焼結法で作られるため、数%のバインダーを含んでいるが、これがコンタミネーションの原因となる場合がある。また、石英製のものは上記欠点は解消されるが、耐蝕性はアルミナ製に比べはるかに低いという欠点がある。従って、これら欠点のない反応容器の開発が望まれる。

【0004】本発明は、上記事情に鑑みなされたもので、耐蝕性及び耐熱衝撃性に優れ、しかも製造時のコンタミネーションもなく、半導体製造分野で有効に使用できる反応容器を提供することを目的とする。

[0005]

【課題を解決するための手段及び発明の実施の形態】本発明者は、上記目的を達成するため鋭意検討を重ねた結果、熱分解窒化硼素で反応容器本体を形成し、かつこの容器本体内壁を窒化アルミニウム、好ましくは結晶子サイズが100nm未満の窒化アルミニウムで被覆することにより、耐蝕性に優れ、酸素やフッ素などの反応性の高いガス種により腐食されることがない上、耐熱衝撃性に優れ、熱衝撃により割れることがなく、かつ上記窒化アルミニウム被覆が剥離してしまうこともなく、しかも製造時のコンタミネーションの心配もない長寿命で高品質の反応容器が得られ、この反応容器は半導体製造用、

特にプラズマCVD反応装置用として極めて有用であることを見出した。

【0006】即ち、本発明者は、熱分解窒化硼素は耐熱 衝撃性が非常に高く、ガス透過性がないことが知られて おり、反応容器として好適な材料であるが、酸素やフッ 素と高温下あるいはプラズマ下で容易に反応し腐食する ことから、このままでは使用できないものであるが、窒 化アルミニウムを熱分解窒化硼素で形成された容器本体 の内壁に被覆することにより、酸素やフッ素で腐食され ることのない優れた耐蝕性が付与されること、それ故、 上記した優れた特性を有し、特にプラズマCVD反応装 置用として有効な反応容器が得られることを知見し、本 発明をなすに至ったものである。

【0007】従って、本発明は、熱分解窒化硼素で形成された反応容器本体内壁に窒化アルミニウムが被覆されてなることを特徴とする反応容器を提供する。

【0008】以下、本発明につき更に詳細に説明する_。 と、本発明の反応容器は、その容器本体が熱分解窒化硼 素で形成されたものである。

【0009】ここで、本発明の反応容器の形状は特に制限はなく、その使用目的に応じた形状とすることができるが、容器内が減圧になる場合、例えばプラズマCVD反応装置用として用いる場合には、円筒状又は半球状とすることが好ましい。

【0010】また、反応容器を形成する熱分解窒化硼素の厚さは $1\sim5\,\mathrm{mm}$ 、特に $2\sim4\,\mathrm{mm}$ の範囲が好ましく、 $1\,\mathrm{mm}$ 未満では強度が不足してしまう場合があり、 $5\,\mathrm{mm}$ より厚いと内部応力により層状に分離してしまう場合がある。

【0011】この場合、熱分解窒化硼素は、化学気相蒸着法により、例えば NH_3 とBC I_3 とのガスを1600~2000C、より好ましくは約1900Cで1~20 Torr、特に約10Torr下で反応させることにより得ることができるもので、この熱分解窒化硼素で反応容器本体を形成するには、所望形状のグラファイト等からなる型を高温炉中に設置し、上記化学気相蒸着法を行った後、でき上がった反応容器本体を型から取り出し、成形することが好適である。

【0012】本発明においては、上記熱分解窒化硼素で 形成された反応容器本体の内壁を窒化アルミニウムで被 覆することが必要である。

【0013】この場合、窒化アルミニウムは結晶子サイズが100nm未満、特に20~40nmのものであることが好ましい。結晶子サイズが100nm以上であると窒化アルミニウムの被覆が剥離しやすくなる場合がある。即ち、窒化アルミニウムは熱分解窒化硼素とは熱膨張係数が異なるため、熱分解窒化硼素に窒化アルミニウムを被覆すると、界面に発生する熱応力により被覆が剥離しやすいが、窒化アルミニウムを結晶子サイズが100nm未満のものとすることで、塑性変形により熱応力

が緩和され剥離が起こらないものである。ここで、上記 結晶子サイズはX線回折で測定した値である。

【0014】また、窒化アルミニウム被膜の厚さは $1\sim50\mu$ m、特に $5\sim20\mu$ mの範囲が好ましく、 1μ m未満では耐蝕性が低下する場合があり、 50μ mより厚いと応力緩和の効果が得られず、剥離が発生する場合がある。

【0015】上記室化アルミニウムによる被覆は、熱分解窒化硼素で形成された反応容器本体を高温炉に設置した後、化学気相蒸着法により、例えば NH_3 と $A1C1_3$ とのガスを1100C以下、特に600~1100C、とりわけ約800Cで1~10Torr、特に6Torr下で反応させることにより得ることができる。なお、窒化アルミニウムの結晶子サイズは反応温度に依存するため、反応温度が1100Cを超えると結晶子サイズが100nm以上になり、窒化アルミニウム被覆の剥離が起こる場合がある。

[0016]

【発明の効果】本発明の反応容器は、酸素やフッ素などの反応性の高いガス種により腐食されることがなく、熱衝撃により割れることもなく、更にはコンタミネーションを発生することもなく、特に窒化アルミニウムを結晶子サイズが100nm未満のものとすることにより、該窒化アルミニウム被覆が剥離してしまうことがないもので、耐蝕性及び耐熱衝撃性に優れ、長寿命で高品質な反応容器である。

[0017]

【実施例】以下、実験例、実施例及び比較例を挙げて本 発明を具体的に説明するが、本発明は下記実施例に制限 されるものではない。

【0018】〔実験例〕化学気相蒸着法により NH_3 と $A1C1_3$ のガスを $600\sim1300$ ℃、6Torr下で反応させ、窒化アルミニウムを得た。この時の反応温度と得られる窒化アルミニウムの結晶子サイズは、図1に示すグラフの通りであった。なお、結晶子サイズは、得られた窒化アルミニウム薄膜をX線回折で分析し、得られた結果(図2)より、その(002)ピークの半値幅から結晶子サイズを求めた。

【0019】図1の結果より、600~1100℃で反応させることにより、結晶子サイズが100nm未満の窒化アルミニウムが得られることが確認された。

【0020】 〔実施例〕 半径99mmの半球状のグラファイトを内径280mm、高さ350mmの円筒状高温炉の中心部に設置した後、炉内を真空ポンプで0.01

Torrまで減圧しながら、炉内温度を10 \mathbb{C}/m in の割合で1900 \mathbb{C} in で昇温した。次に、炉内に NH_3 ガスと $BC1_3$ ガスをそれぞれ12L/m in 、3L/m in の割合で供給し、炉内温度1900 \mathbb{C} 、炉内圧力10 \mathbb{C} 、炉内压力10 \mathbb{C} 、炉内压力10 \mathbb{C} 、炉内温度を3 \mathbb{C}/m in の割合で室温まで冷却した後、反応により生成した熱分解窒化硼素が表面に堆積したグラファイト半球を取り出した。次に、グラファイト半球から熱分解窒化硼素を取りはずし、機械加工により整形し、内径100 \mathbb{C} \mathbb{C}

【0022】このものを図3に示すような準常圧プラズマCVD反応装置の反応容器として使用した。なお、図3において、1は中空半球状の反応容器、2はウエハ載置台、3はウエハ、4は原料供給ノズル、5はプラズマ発生装置である。

【0023】次に、準常圧プラズマCVD反応装置の反応容器として使用した際の耐蝕性、耐熱衝撃性を評価したところ、上記反応容器は、酸素やフッ素には侵食されず、50℃/minの熱衝撃にも割れず、被覆の剥離も起こらず、コンタミネーションも全く認められなかった

【0024】また、上記実施例と同形状、同様の方法で表1に示すように熱分解窒化硼素の厚さ、窒化アルミニウム被覆の厚さ、結晶子サイズを変えて反応容器を作り、同様に準常圧プラズマCVD反応装置の反応容器として使用したところ、表1に示す結果が得られた。

【表1】

[0025]

熱分解窒化硼素	窒化アル	ミニウム被覆	TIALM.	耐熱衝撃性	
厚 さ (mm)	厚さ (µm)	結晶子サイズ (nm)	耐蝕性		
0.8	60	30	良好	割れが少しあり	
1	10	30	良好	良好	
5	10	30	良好	良好	
6	10	30	良好	層状分離が少しあり	
3	0.5	30	耐蝕性が若干劣る	良好	
3	10	30	良好	良好	
3	50	30	良好	良好	
3	60	30	良好	剥離が少しあり	
3	10	30	良好	良好	
3	10	90	良好	良好	
3	10	100	良好	剥離あり	

【0026】表1の結果より、熱分解窒化硼素の厚さが $1\sim5\,\mathrm{mm}$ 、窒化アルミニウム被覆の厚さが $1\sim50\,\mu$ m、結晶子サイズが $100\,\mu$ m未満である反応容器は、とりわけ耐蝕性、耐熱衝撃性に優れていることがわかった。

【図面の簡単な説明】

【図1】窒化アルミニウム被覆形成時の反応温度と結晶 子サイズとの関係を示すグラフである。

【図2】 窒化アルミニウム被覆のX線回折チャートを示

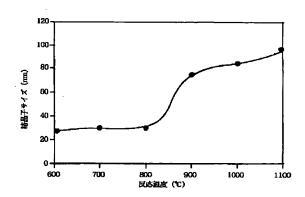
すグラフである。

【図3】プラズマCVD反応装置の一例を示す概略図である。

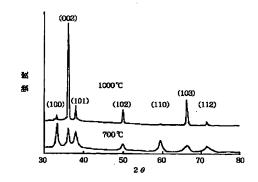
【符号の説明】

- 1 反応容器
- 2 ウエハ載置台
- 3 ウエハ
- 4 原料供給ノズル
- 5 プラズマ発生装置

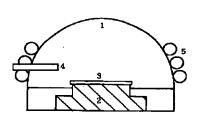




【図2】



【図3】



フロントページの続き

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25/08



CLAIMS DETAILED DESCRIPTION TECHNICAL FIELD PRIOR ART EFFECT OF THE INVENTION TECHNICAL PROBLEM EXAMPLE DESCRIPTION OF DRAWINGS DRAWINGS

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CLAIMS

[Claim(s)]

[Claim 1] The reaction container characterized by the wall of the body of a reaction container formed by pyrolysis boron nitride coming to cover alumimium nitride.

[Claim 2] The reaction container according to claim 1 whose microcrystal size of the alumimium nitride covered by the wall is less than 100nm.

[Claim 3] The reaction container according to claim 1 or 2 which is an object for plasma-CVD reactors.



<u>CLAIMS DETAILED DESCRIPTION TECHNICAL FIELD PRIOR ART EFFECT OF THE INVENTION TECHNICAL PROBLEM EXAMPLE DESCRIPTION OF DRAWINGS DRAWINGS</u>

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DETAILED DESCRIPTION

[Detailed Description of the Invention]

[0001]

[Field of the Invention] This invention relates to the reaction container which was excellent in corrosion resistance, thermal shock resistance, etc. at the detail further about a reaction container suitable as the semi-conductor manufacture field, especially an object for plasma-CVD reactors.

[0002]

[Description of the Prior Art] Conventionally, although the metal has been adopted as the construction material of that reaction container in a plasma-CVD reactor, since the reaction using a reactant high type of gas, for example, O, and F has increased, there is a motion changed to the corrosion-resistant high ceramics from the metal which is easy to corrode the construction material of this reaction container in recent years. Specifically, the reaction container made from the product made from an alumina or a quartz is beginning to be adopted.

[0003]

[Problem(s) to be Solved by the Invention] However, if a reaction container is made into the thing made from an alumina, although corrosion resistance will improve by leaps and bounds, thermal shock resistance of an alumina is low, and it cannot bear the temperature change by the reaction, but has the fault of being divided easily. Furthermore, although several% of binder is included since the thing made from an alumina is usually made with a sintering process, this may cause contamination. Moreover, although the above-mentioned fault is canceled for the thing made from a quartz, corrosion resistance is compared with the product made from an alumina, and has the fault of being far low. Therefore, development of a reaction container without these faults is desired.

[0004] This invention was made in view of the above-mentioned situation, is excellent in corrosion resistance and thermal shock resistance, moreover does not have the contamination at the time of manufacture, either, and aims at offering the reaction container which can be effectively used in the semi-conductor manufacture field.

[The means for solving a technical problem and the gestalt of implementation of invention] In order that this invention person may attain the above-mentioned object, as a result of repeating examination wholeheartedly, the body of a reaction container is formed by pyrolysis boron nitride. This body wall of a container and alumimium nitride and when microcrystal size covers with less than 100nm alumimium nitride preferably When it excels in corrosion resistance and is not corroded by the reactant high type of gas of oxygen, a fluorine, etc., Without excelling in thermal shock resistance, and not being divided by the thermal shock, and the above-mentioned alumimium nitride coat exfoliating And it was long lasting, the reaction container of high quality was obtained, and this reaction container found out the thing very useful as the object for semi-conductor manufacture, especially an object for plasma-CVD reactors also without worries about the contamination at the time of manufacture.

[0006] Namely, although pyrolysis boron nitride has dramatically high thermal shock resistance, it is known that there is no gas permeability and this invention person is an ingredient suitable as a reaction container Although it cannot be used the way things stand since it reacts easily and corrodes under oxygen, a fluorine, an elevated temperature, or the plasma By covering alumimium nitride to the wall of the body of a container formed by pyrolysis boron nitride So it has that the outstanding corrosion resistance corroded neither with oxygen nor a fluorine is given, and the above-mentioned outstanding property, the knowledge of the effective reaction container as an object for plasma-CVD reactors being obtained especially is carried out, and it comes to make this invention.

[0007] Therefore, this invention offers the reaction container characterized by the body wall of a reaction container formed by pyrolysis boron nitride coming to cover aluminium nitride.

[0008] Hereafter, if it explains per this invention and also to a detail, as for the reaction container of this invention, the body of a container will be formed by pyrolysis boron nitride.

[0009] Although especially a limit does not have the configuration of the reaction container of this invention and it can consider as the configuration where it responded in activity eye here, when the inside of a container is decompressed (for example, when using as an object for plasma-CVD reactors), it is desirable to suppose that it is cylindrical or hemispherical.

[0010] Moreover, 1-5mm, especially the thickness of the pyrolysis boron nitride which forms a reaction container has the desirable range of 2-4mm, and by less than 1mm, if reinforcement may be insufficient and it is thicker than 5mm, internal stress may separate it in the shape of a layer.

[0011] Pyrolysis boron nitride the gas of NH3 and BCl3 with chemistry gaseous-phase vacuum deposition In this case, 1600-2000 degrees C, In order to be able to obtain one to 20 Torr by making it react under about 10 Torr(s) at about 1900 degrees C especially more preferably and to form the body of a reaction container by this pyrolysis boron nitride After installing the mold which consists of graphite of a request configuration etc. all over an elevated-temperature furnace and performing the above-mentioned chemistry gaseous-phase vacuum deposition, it is suitable the ejection from a mold and to fabricate the done body of a reaction container.

[0012] In this invention, it is required to cover with alumimium nitride the wall of the body of a reaction container formed by the above-mentioned pyrolysis boron nitride.

[0013] In this case, as for especially alumimium nitride, it is desirable that less than 100nm of microcrystal sizes is what is 20-40nm. The coat of alumimium nitride becomes it easy to exfoliate that microcrystal size is 100nm or more. That is, although, as for alumimium nitride, a coat tends to exfoliate with the thermal stress which will generate pyrolysis boron nitride in an interface if alumimium nitride is covered to pyrolysis boron nitride, since coefficients of thermal expansion differ, microcrystal size is considering as a less than 100nm thing, thermal stress is eased by plastic deformation and exfoliation does not take place alumimium nitride. Here, the above-mentioned microcrystal size is the value measured by the X diffraction.

[0014] Moreover, especially the thickness of an alumimium nitride coat has the desirable range of 5-20 micrometers, and in less than 1 micrometer, corrosion resistance may fall, if thicker than 50 micrometers, the effectiveness of stress relaxation is not acquired, but 1-50 micrometers of exfoliations may generate it.

[0015] The coat by the above-mentioned alumimium nitride can obtain 600-1100 degrees C of 1100 degrees C or less of gas of NH3 and AlCl3 with chemistry gaseous-phase vacuum deposition by making it especially react especially under 6Torr(s) one to 10 Torr at about 800 degrees C, after installing the body of a reaction container formed by pyrolysis boron nitride in an elevated-temperature furnace. In addition, since it depends for the microcrystal size of alumimium nitride on reaction temperature, if reaction temperature exceeds 1100 degrees C, microcrystal size may be set to 100nm or more, and exfoliation of an alumimium nitride coat may take place.

[0016]

[Effect of the Invention] Without generating contamination further, without not being corroded by the reactant high type of gas of oxygen, a fluorine, etc., and being divided by the thermal shock, when microcrystal size makes especially alumimium nitride a less than 100nm thing, this alumimium nitride coat does not exfoliate, and the reaction container of this invention is excellent in corrosion resistance and thermal shock resistance, and is a long lasting and quality reaction container.

[0017]

[Example] Although the example of an experiment, an example, and the example of a comparison are given and this invention is explained concretely hereafter, this invention is not restricted to the following example.

[0018] [Example of an experiment] The gas of NH3 and AlCl3 was made to react under 600-1300 degrees C and 6Torr with chemistry gaseous-phase vacuum deposition, and alumimium nitride was obtained. The reaction temperature at this time and the microcrystal size of the alumimium nitride obtained were as the graph shown in <u>drawing 1</u>. In addition, microcrystal size analyzed the obtained alumimium nitride thin film by the X diffraction, and asked for microcrystal size from the (002) full width at half maximum from the obtained result (drawing 2).

[0019] From the result of <u>drawing 1</u>, it was checked by making it react at 600-1100 degrees C that less than 100nm alumimium nitride is obtained for microcrystal size.

[0020] half [Example] — temperature up of whenever [furnace temperature] was carried out to 1900 degrees C at a rate of 10 degrees C / min, decompressing the inside of a furnace to 0.01Torr(s) with a vacuum pump, after installing the graphite of the shape of a path 99mm semi-sphere in the core of a cylindrical elevated-temperature furnace with a bore [of 280mm], and a height of 350mm. Next, NH3 gas and BCl3 gas were supplied at a rate of 12 L/min and 3 L/min in the furnace, respectively, and the reaction was performed for 25 hours, adjusting to 1900 degrees C and furnace internal pressure 10Torr whenever [furnace temperature]. After cooling whenever [furnace temperature] to a room temperature at a rate of 3 degrees C / min, the pyrolysis boron nitride generated by the reaction took out the graphite semi-sphere deposited on the front face. Next, pyrolysis boron nitride was orthopedically operated by disconnection and machining from the graphite semi-sphere, and the pyrolysis boron nitride of the shape of a hollow semi-sphere with a bore [of 100mm] and a thickness of 3mm was obtained.

[0021] Next, temperature up of whenever [furnace temperature] was carried out to 800 degrees C at a rate of 10 degrees C / min, decompressing the inside of a furnace to 0.01Torr(s) with a vacuum pump, after installing the obtained pyrolysis boron nitride in the core of a cylindrical elevated-temperature furnace with a bore [of 300mm], and a height of 500mm. Furthermore, AICl3 gas which NH3 gas and 140 degrees C were made to heat and sublimate into a furnace was supplied at a rate of 3 L/min and 0.3 L/min, respectively, and the reaction was performed for 30 minutes, adjusting to 800 degrees C and furnace internal pressure 6Torr whenever [furnace temperature]. After cooling whenever [furnace temperature] to a room temperature at a rate of 3 degrees C / min, the pyrolysis boron nitride of the shape of a hollow semi-sphere by which the inner surface was covered with the alumimium nitride generated by the reaction was taken out. The thickness of this alumimium nitride coat was 10 micrometers, and microcrystal size was 30nm. In addition, the measuring method of microcrystal size was based on the X-ray diffraction method.

[0022] It was used as a reaction container of a semi- ordinary pressure plasma-CVD reactor as shows this thing to drawing 3. In addition, for a hollow semi-sphere-like reaction container and 2, as for a wafer and 4, in drawing 3, a wafer installation base and 3 are [1 / a feeding nozzle and 5] plasma generators.

[0023] Next, when the corrosion resistance at the time of using it as a reaction container of a semi- ordinary pressure plasma-CVD reactor and thermal shock resistance were evaluated, the above-mentioned reaction container was eaten away by neither oxygen nor the fluorine, it was not divided into the thermal shock of 50 degrees C / min, exfoliation of a coat did not take place, either, and contamination was not accepted at all, either.

[0024] Moreover, when the thickness of pyrolysis boron nitride, the thickness of an alumimium nitride coat, and microcrystal size were changed by the shape of the above-mentioned example and isomorphism, and the same approach as shown in a table 1, the reaction container was made and it was similarly used as a reaction container of a semi-ordinary pressure plasma-CVD reactor, the result shown in a table 1 was obtained.

[A table 1]

[0025]

熱分解窒化砌素	窒化アル	ミニウム被覆	TIALIN.	耐熱衝撃性	
厚さ (mm)	厚 さ (µm)	結晶子サイズ (nm)	耐蝕性		
0.8	60	30	良好	割れが少しあり	
1	10	30	良好	良好	
5	10	30	良好	良好	
6	10	30	良好	層状分離が少しあり	
3	0.5	80	耐蝕性が若干劣る	良好	
3	10	30	良好	良好	
3	50	30	良好	良好	
3	60	30	良好	剥離が少しあり	
3	10	30	良好	良好	
3	10	90	良好	良好	
3	10	100	良好	剥離あり	

[0026] The result of a table 1 showed that the reaction container 1-50 micrometers and whose microcrystal size the thickness of 1-5mm and an alumimium nitride coat is less than 100 micrometers especially excelled [thickness / of pyrolysis boron nitride] in corrosion resistance and thermal shock resistance.



CLAIMS DETAILED DESCRIPTION TECHNICAL FIELD PRIOR ART EFFECT OF THE INVENTION TECHNICAL PROBLEM EXAMPLE DESCRIPTION OF DRAWINGS DRAWINGS

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DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[<u>Drawing 1</u>] It is the graph which shows the relation between the reaction temperature at the time of alumimium nitride coat formation, and microcrystal size.

[Drawing 2] It is the graph which shows the X diffraction chart of an alumimium nitride coat.

[Drawing 3] It is the schematic diagram showing an example of a plasma-CVD reactor.

[Description of Notations]

- 1 Reaction Container
- 2 Wafer Installation Base
- 3 Wafer
- 4 Feeding Nozzle
- 5 Plasma Generator